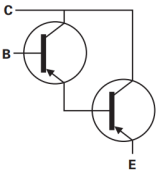
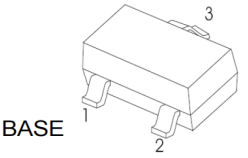
PNP Silicon Darlington Transistors



- For general AF applications
- High collector current
- High current gain
- Complementary types: BCV27, BCV47 (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



SOT-23

Type	Marking	Pin Configuration			Package
BCV26	FDs	1=B	2=E	3=C	SOT-23
BCV46	ZFE	1=B	2=E	3=C	SOT-23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$-V_{CEO}$		V
BCV26		30	
BCV46		60	
Collector-base voltage	$-V_{CBO}$		
BCV26		40	
BCV46		80	
Emitter-base voltage	$-V_{EBO}$	10	
Collector current	$-I_C$	500	mA
Peak collector current, $t_p \leq 10$ ms	$-I_{CM}$	800	
Base current	$-I_B$	100	
Peak base current	$-I_{BM}$	200	
Total power dissipation- $T_S \leq 74$ °C	P_{tot}	360	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 210	K/W

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$-V_{(BR)CEO}$				V
$-I_C$ = 10 mA, $-I_B$ = 0 , BCV26		30	-	-	
$-I_C$ = 10 mA, $-I_B$ = 0 , BCV46		60	-	-	
Collector-base breakdown voltage	$-V_{(BR)CBO}$				
$-I_C$ = 100 µA, $-I_E$ = 0 , BCV26		40	-	-	
$-I_C$ = 100 µA, $-I_E$ = 0 , BCV46		80	-	-	
Emitter-base breakdown voltage	$-V_{(BR)EBO}$	10	-	-	
$-I_E$ = 10 µA, $-I_C$ = 0					
Collector-base cutoff current	$-I_{CBO}$				µA
$-V_{CB}$ = 30 , $-I_E$ = 0 , BCV26		-	-	0.1	
$-V_{CB}$ = 60 , $-I_E$ = 0 , BCV46		-	-	0.1	
$-V_{CB}$ = 30 , $-I_E$ = 0 , T_A = 150 °C, BCV26		-	-	10	
$-V_{CB}$ = 60 , $-I_E$ = 0 , T_A = 150 °C, BCV46		-	-	10	
Emitter-base cutoff current	$-I_{EBO}$	-	-	100	nA
$-V_{EB}$ = 4 V, $-I_C$ = 0					
DC current gain [1)]	h_{FE}				-
$-I_C$ = 100 µA, $-V_{CE}$ = 1 V, BCV26		4000	-	-	
$-I_C$ = 100 µA, $-V_{CE}$ = 1 V, BCV46		2000	-	-	
$-I_C$ = 10 mA, $-V_{CE}$ = 5 V, BCV26		10000	-	-	
$-I_C$ = 10 mA, $-V_{CE}$ = 5 V, BCV46		4000	-	-	
$-I_C$ = 100 mA, $-V_{CE}$ = 5 V, BCV26		20000	-	-	
$-I_C$ = 100 mA, $-V_{CE}$ = 5 V, BCV46		10000	-	-	
$-I_C$ = 0.5 A, $-V_{CE}$ = 5 V, BCV26		4000	-	-	
$-I_C$ = 0.5 A,- V_{CE} = 5 V, BCV46		2000	-	-	
Collector-emitter saturation voltage [1)]	$-V_{CEsat}$	-	-	1	V
$-I_C$ = 100 mA, $-I_B$ = 0.1 mA					
Base emitter saturation voltage [1)]	$-V_{BEsat}$	-	-	1.5	
$-I_C$ = 100 mA, $-I_B$ = 0.1 mA					

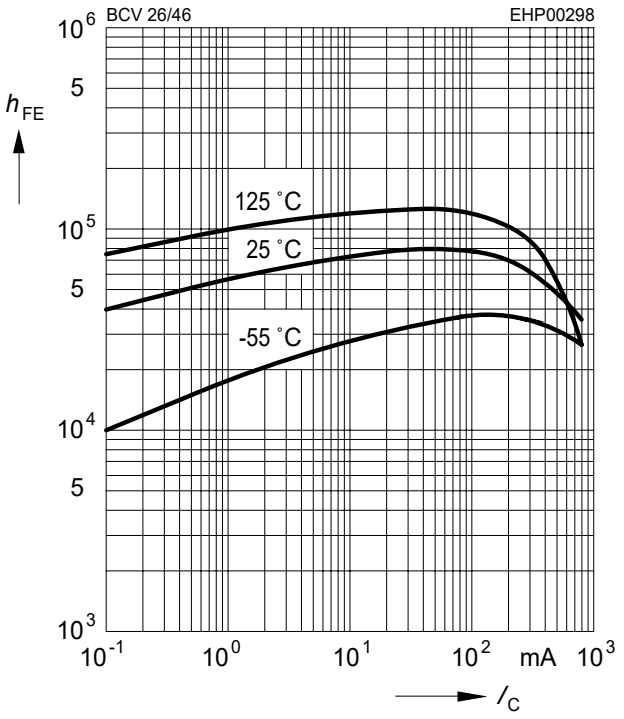
[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $-I_C$ = 50 mA, $-V_{CE}$ = 5 V, f = 100 MHz	f_T	-	200	-	MHz
Collector-base capacitance $-V_{CB}$ = 10 V, f = 1 MHz	C_{cb}	-	4.5	-	pF

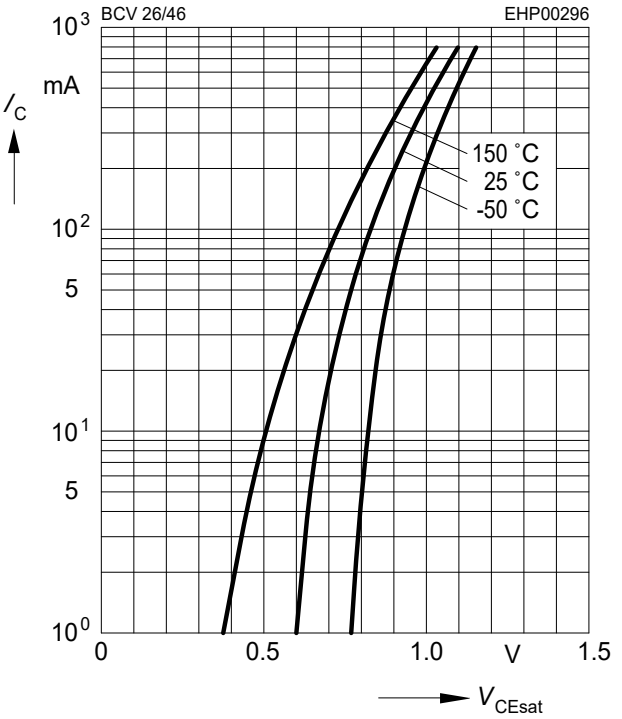
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 5 V



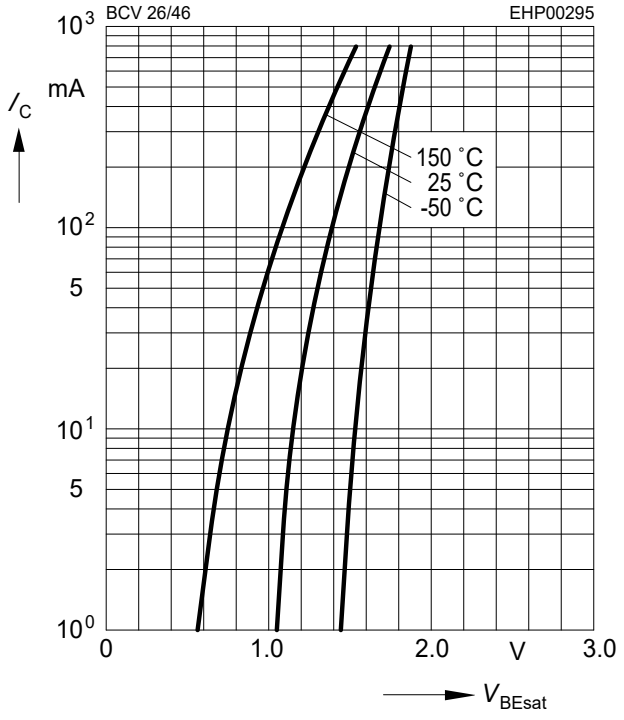
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 1000



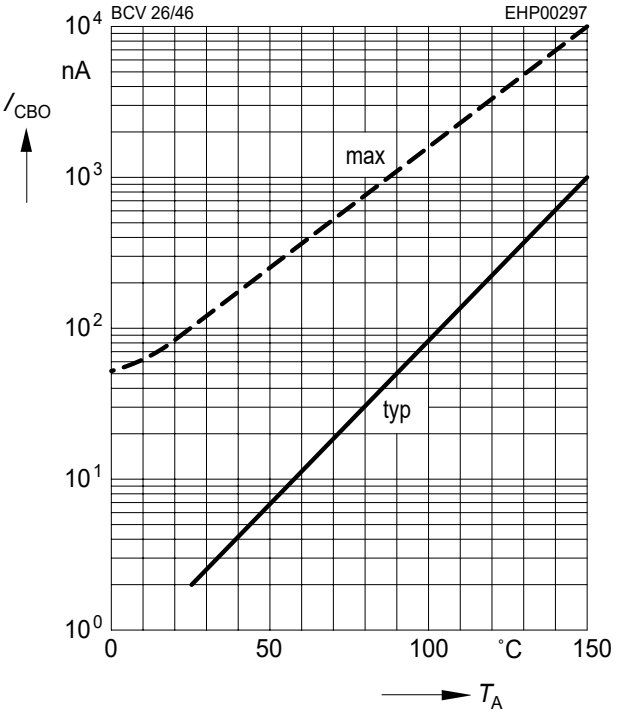
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 1000

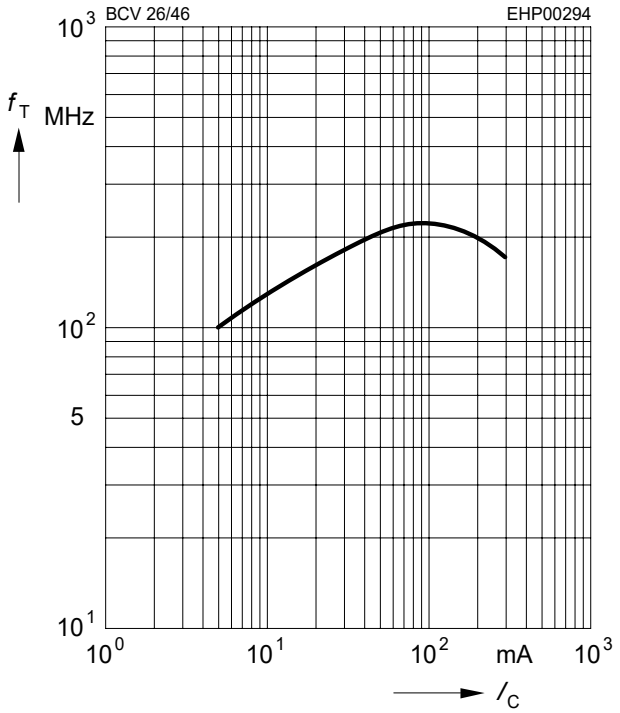


Collector cutoff current $I_{CBO} = f(T_A)$

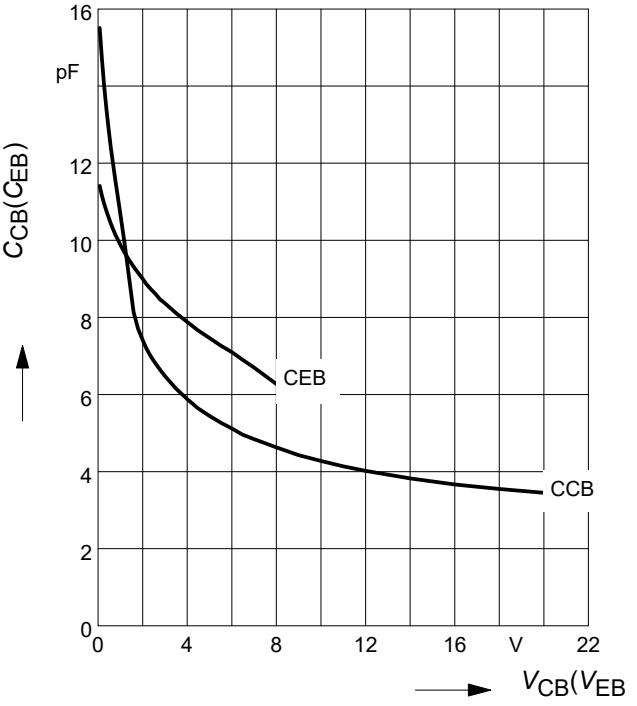
$V_{CB} = V_{CEmax}$



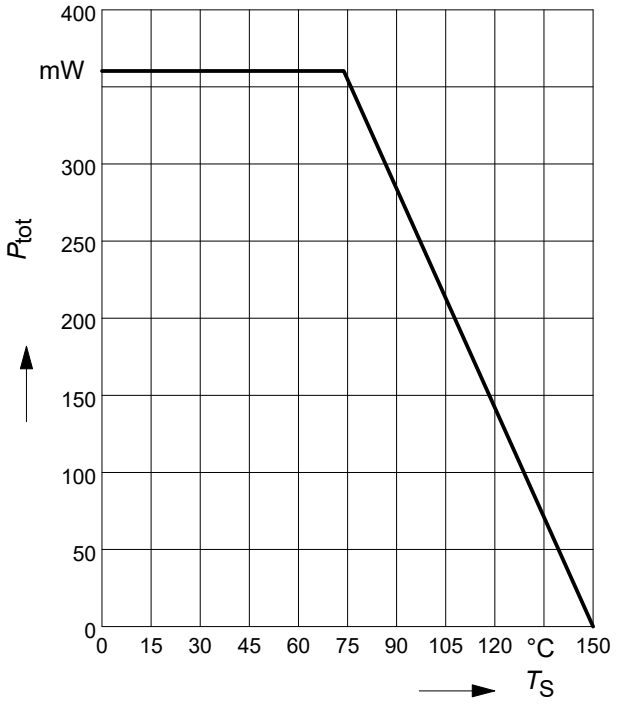
Transition frequency $f_T = f(I_C)$
V_{CE} = 5 V



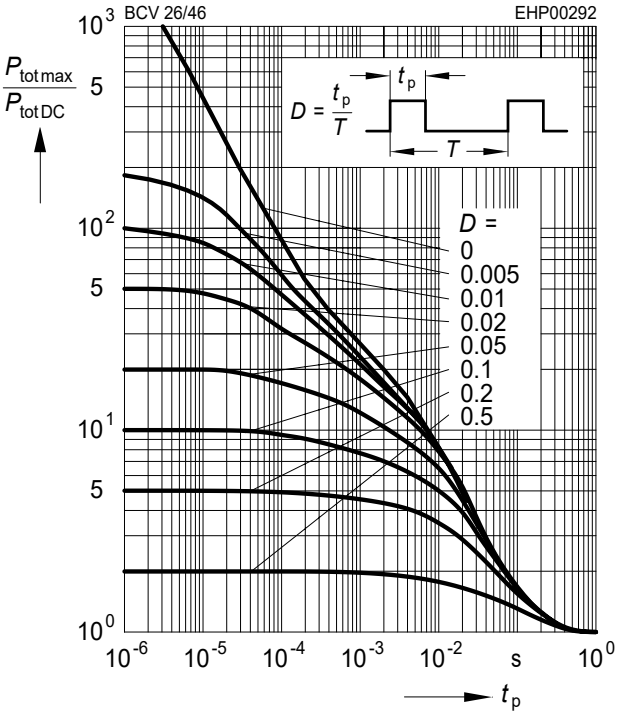
Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

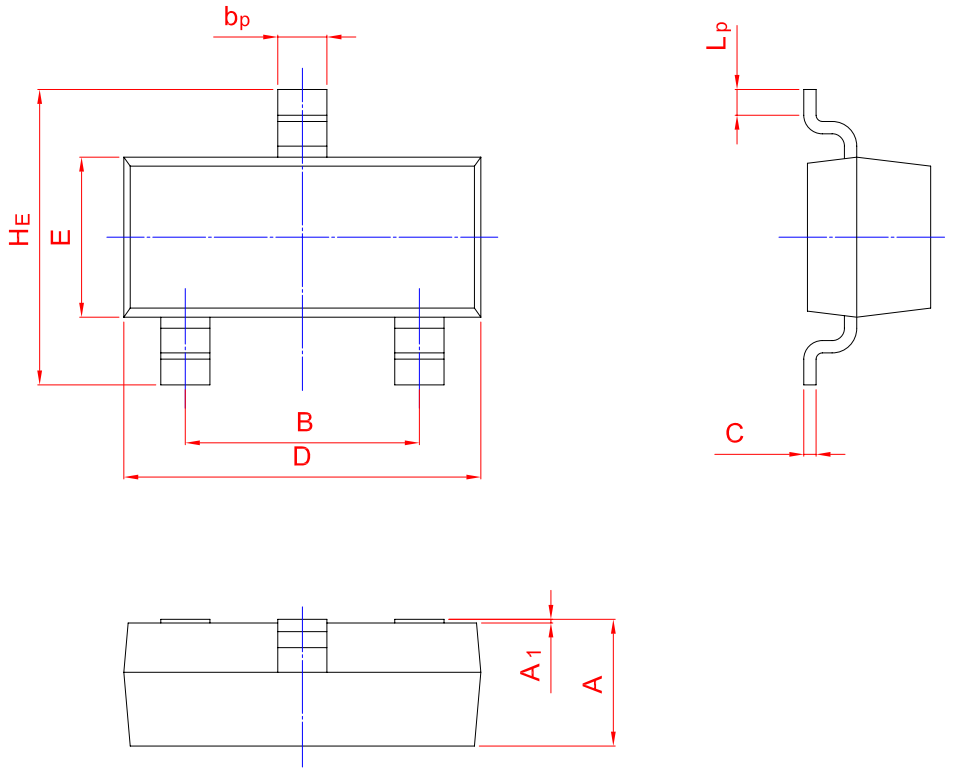


Permissible Pulse Load
$P_{totmax}/P_{totDC} = f(t_p)$



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20